ALPHA & OMEGA SEMICONDUCTOR

AOT20S60/AOB20S60/AOTF20S60

600V 20A αMOS™ Power Transistor

General Description

The AOT20S60& AOB20S60 & AOTF20S60 have been fabricated using the advanced αMOS™ high voltage process that is designed to deliver high levels of performance and robustness in switching applications. By providing low $R_{DS(on)}$, Q_g and E_{OSS} along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

For Halogen Free add "L" suffix to part number: AOT20S60L & AOB20S60L & AOTF20S60L

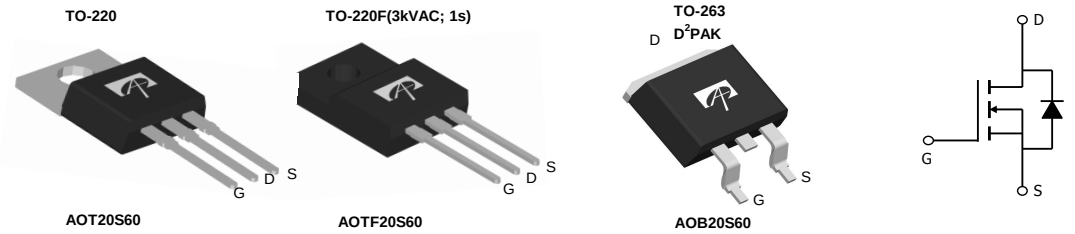
Product Summary

V_{DS} @ $T_{j,max}$	700V
I_{DM}	80A
$R_{DS(ON),max}$	0.199Ω
$Q_{g,typ}$	20nC
E_{oss} @ 400V	4.9µJ

100% UIS Tested
100% R_g Tested

RoHS Compliant

Top View



Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter		Symbol	AOT20S60/AOB20S60	AOTF20S60	AOTF20S60L	Units
Drain-Source Voltage		V_{DS}	600			V
Gate-Source Voltage		V_{GS}	±30			V
Continuous Drain Current	T_C=25℃	I_D	20	20*	20*	A
	T_C=100℃		14	14*	14*	
Pulsed Drain Current [C]		I_{DM}	80			
Avalanche Current [C]		I_{AR}	3.4			A
Repetitive avalanche energy [C]		E_{AR}	23			mJ
Single pulsed avalanche energy [G]		E_{AS}	188			mJ
Power Dissipation [B]	T_C=25℃	P_D	266	50	37.8	W
	Derate above 25°C		2.1	0.4	0.3	W/°C
MOSFET dv/dt ruggedness		dv/dt	100			V/ns
Peak diode recovery dv/dt [H]			20			
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150			℃
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds [J]		T_L	300			℃

Thermal Characteristics

Parameter	Symbol	AOT20S60/AOB20S60	AOTF20S60	AOTF20S60L	Units
Maximum Junction-to-Ambient [A,D]	$R_{\theta JA}$	65	65	65	℃/W
Maximum Case-to-sink [A]	$R_{\theta CS}$	0.5	--	--	℃/W
Maximum Junction-to-Case	$R_{\theta JC}$	0.47	2.5	3.3	℃/W

* Drain current limited by maximum junction temperature.

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V, T_J=25°C	600	-	-	V
		I_D=250µA, V_{GS}=0V, T_J=150°C	650	700	-	
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=600V, V_{GS}=0V	-	-	1	µA
		V_{DS}=480V, T_J=150°C	-	10	-	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±30V	-	-	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=5V,I_D=250µA	2.8	3.4	4.1	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=10A, T_J=25°C	-	0.18	0.199	Ω
		V_{GS}=10V, I_D=10A, T_J=150°C	-	0.48	0.53	Ω
V_{SD}	Diode Forward Voltage	I_S=10A,V_{GS}=0V, T_J=25°C	-	0.84	-	V
I_S	Maximum Body-Diode Continuous Current		-	-	20	A
I_{SM}	Maximum Body-Diode Pulsed Current[C]		-	-	80	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=100V, f=1MHz	-	1038	-	pF
C_{oss}	Output Capacitance		-	68	-	pF
$C_{o(er)}$	Effective output capacitance, energy related[H]	V_{GS}=0V, V_{DS}=0 to 480V, f=1MHz	-	56.6	-	pF
$C_{o(tr)}$	Effective output capacitance, time related[I]		-	176.5	-	pF
C_{rss}	Reverse Transfer Capacitance	V_{GS}=0V, V_{DS}=100V, f=1MHz	-	2.1	-	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	-	9.3	-	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=480V, I_D=10A	-	19.8	-	nC
Q_{gs}	Gate Source Charge		-	4.6	-	nC
Q_{gd}	Gate Drain Charge		-	7.6	-	nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=400V, I_D=10A, R_G=25Ω	-	27.5	-	ns
t_r	Turn-On Rise Time		-	32	-	ns
$t_{D(off)}$	Turn-Off DelayTime		-	87.5	-	ns
t_f	Turn-Off Fall Time		-	30	-	ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=10A,dI/dt=100A/µs,V_{DS}=400V	-	350	-	ns
I_{rm}	Peak Reverse Recovery Current	I_F=10A,dI/dt=100A/µs,V_{DS}=400V	-	27	-	A
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=10A,dI/dt=100A/µs,V_{DS}=400V	-	5.7	-	µC

A. The value of $R_{\theta JA}$ is measured with the device in a still air environment with T_A =25°C.

B. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C, Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 µs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C. The SOA curve provides a single pulse ratin g.

G. L=60mH, I_{AS}=2.5A, V_{DD}=150V, Starting T_J=25°C

H. $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$.

I. $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$.

J. Wavesoldering only allowed at leads.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

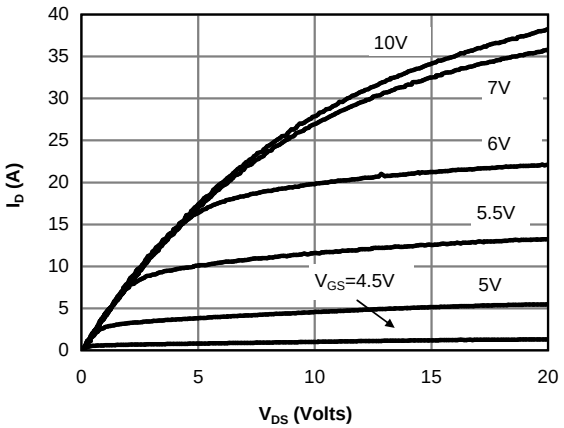


Figure 1: On-Region Characteristics@25℃

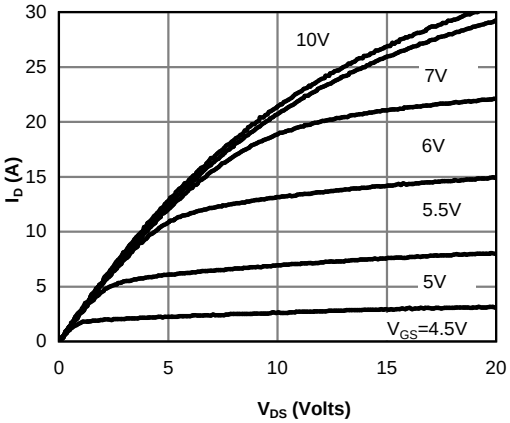


Figure 2: On-Region Characteristics@125℃

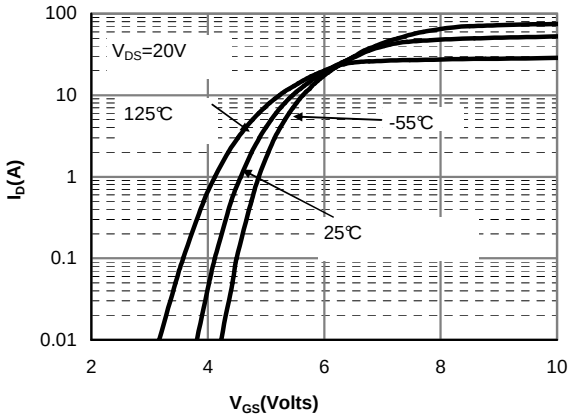


Figure 3: Transfer Characteristics

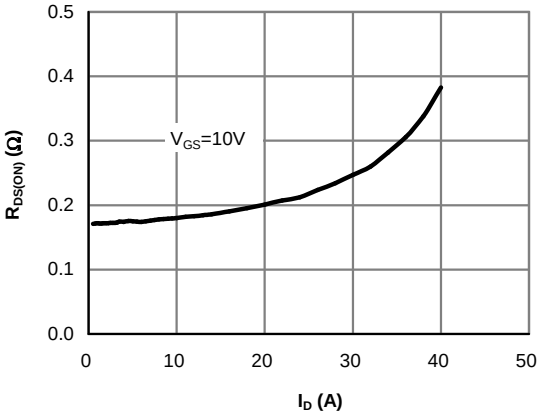


Figure 4: On-Resistance vs. Drain Current and Gate Voltage

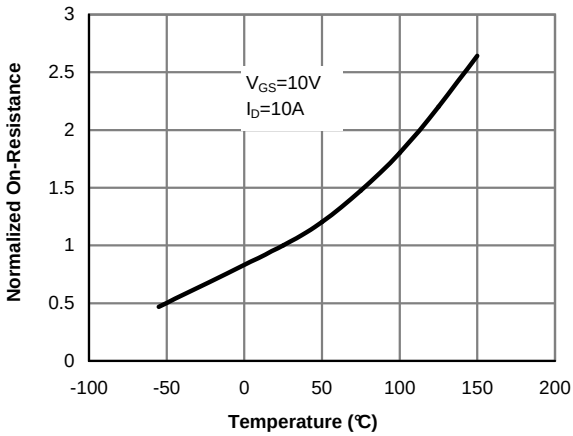


Figure 5: On-Resistance vs. Junction Temperature

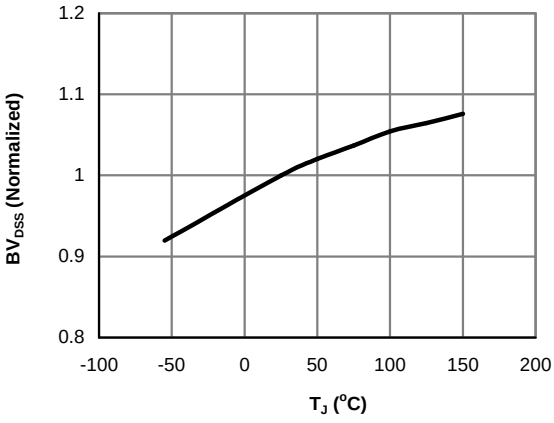


Figure 6: Break Down vs. Junction Temperature

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

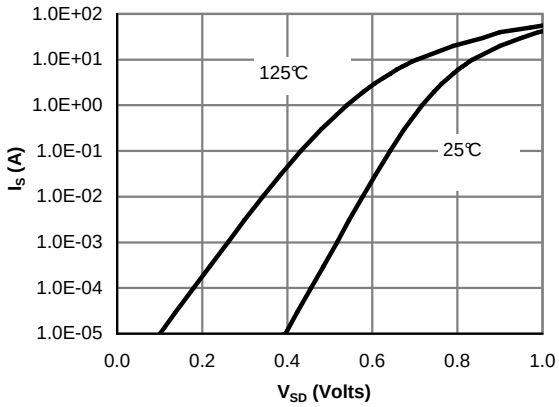


Figure 7: Body-Diode Characteristics (Note E)

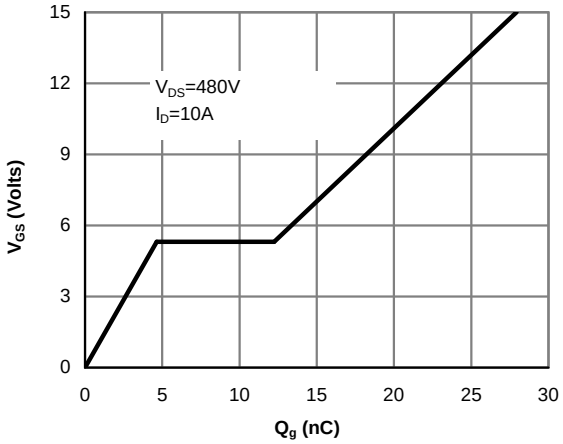


Figure 8: Gate-Charge Characteristics

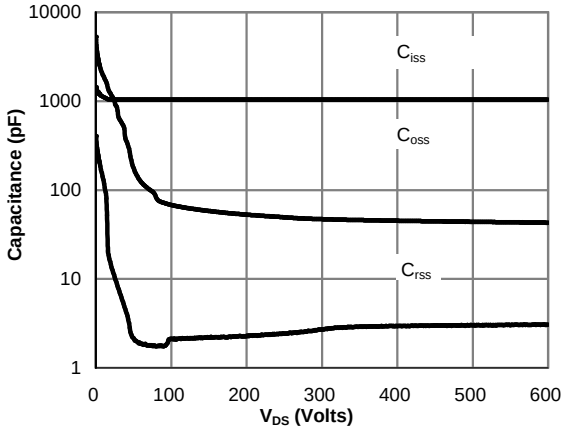


Figure 9: Capacitance Characteristics

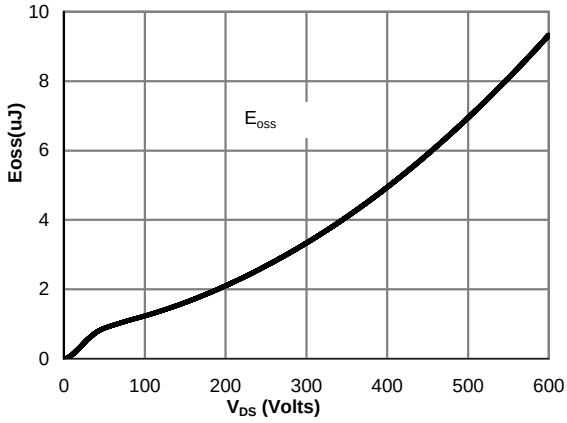


Figure 10: Coss stored Energy

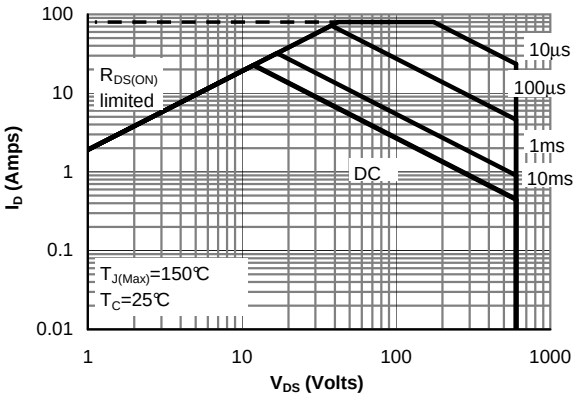


Figure 11: Maximum Forward Biased Safe Operating Area for AOT(B)20S60 (Note F)

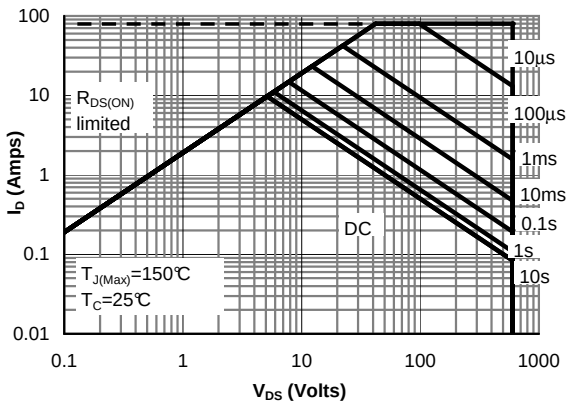


Figure 12: Maximum Forward Biased Safe Operating Area for AOTF20S60(Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

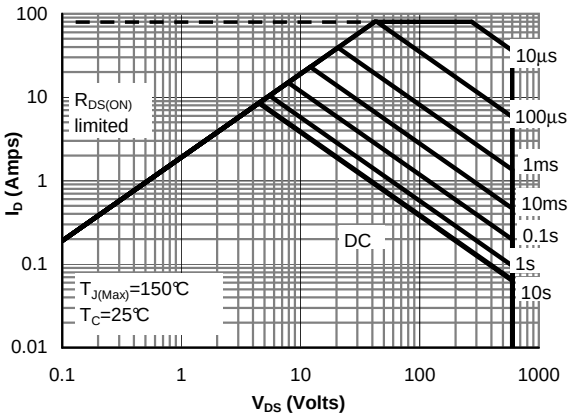


Figure 13: Maximum Forward Biased Safe Operating Area for AOTF20S60L(Note F)

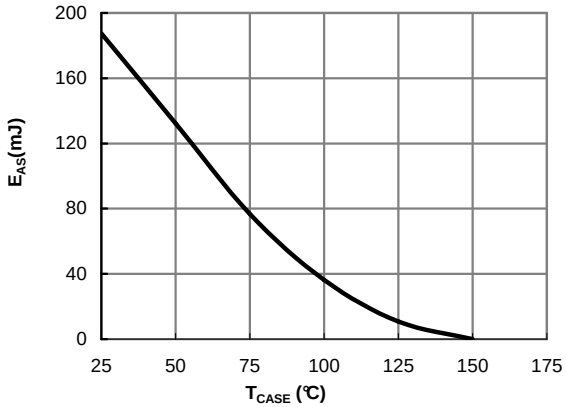


Figure 14: Avalanche energy

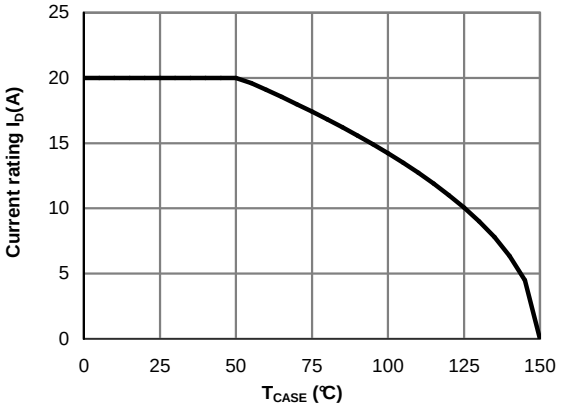


Figure 15: Current De-rating (Note B)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

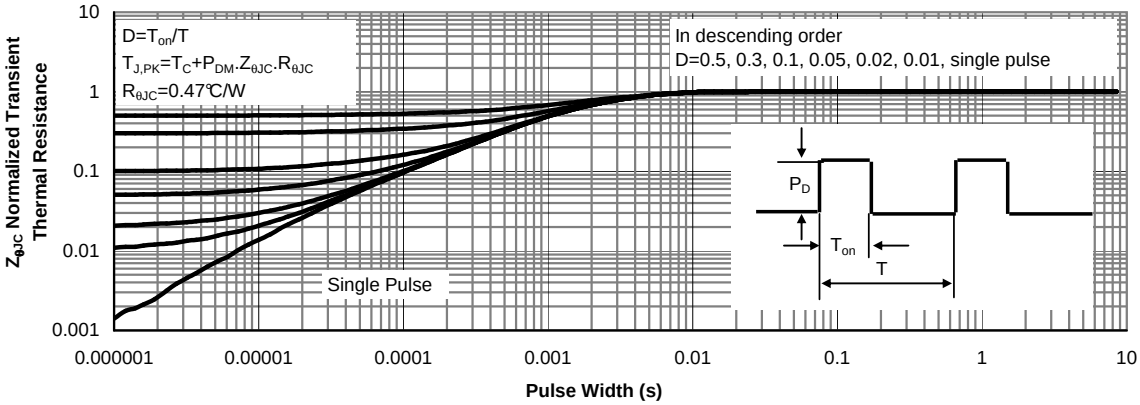


Figure 16: Normalized Maximum Transient Thermal Impedance for AOT(B)20S60 (Note F)

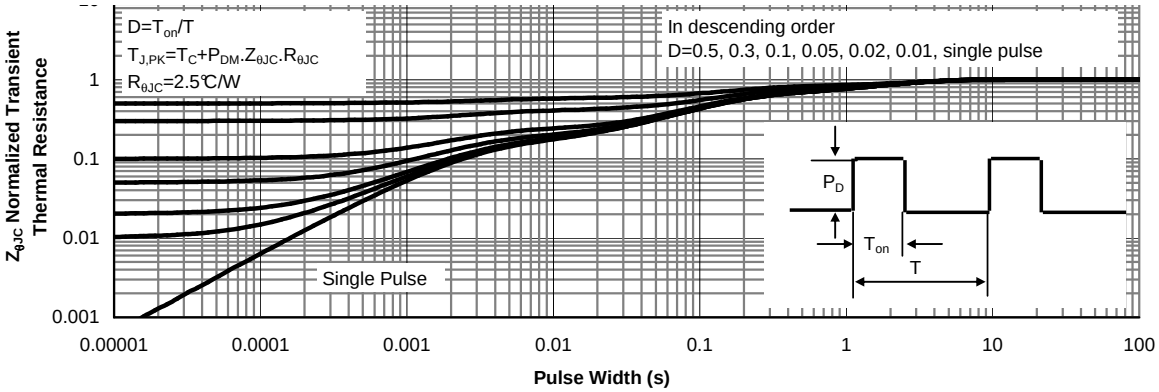


Figure 17: Normalized Maximum Transient Thermal Impedance for AOTF20S60 (Note F)

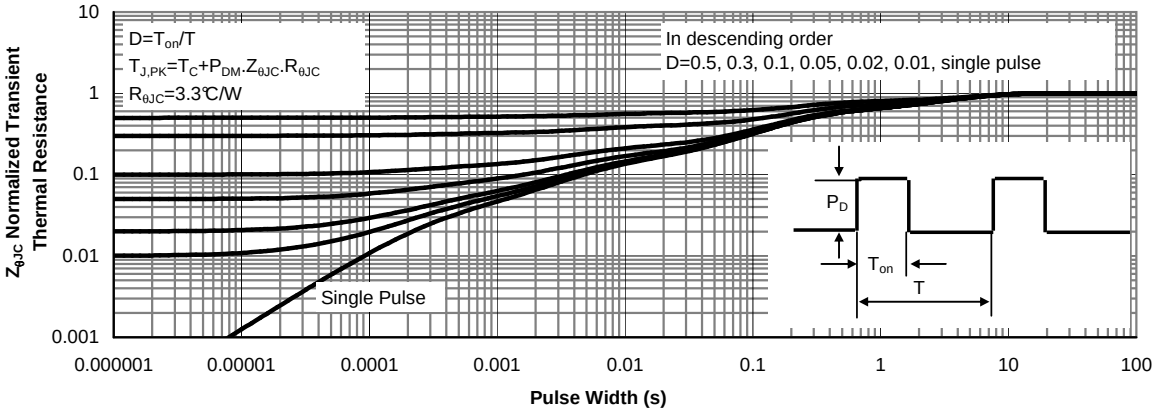
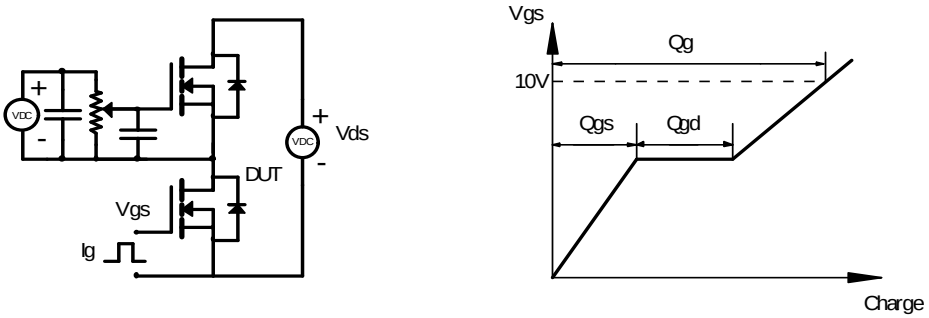
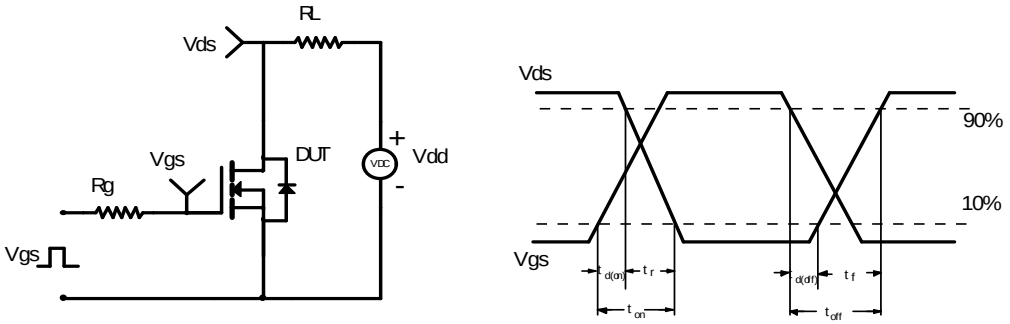


Figure 18: Normalized Maximum Transient Thermal Impedance for AOTF20S60L (Note F)

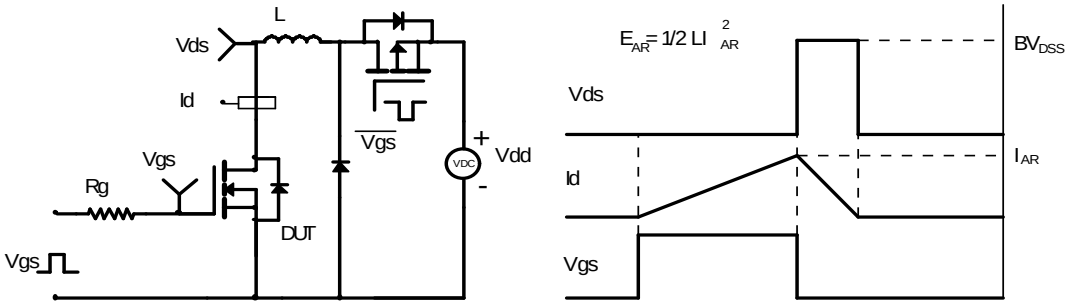
Gate Charge Test Circuit & Waveform



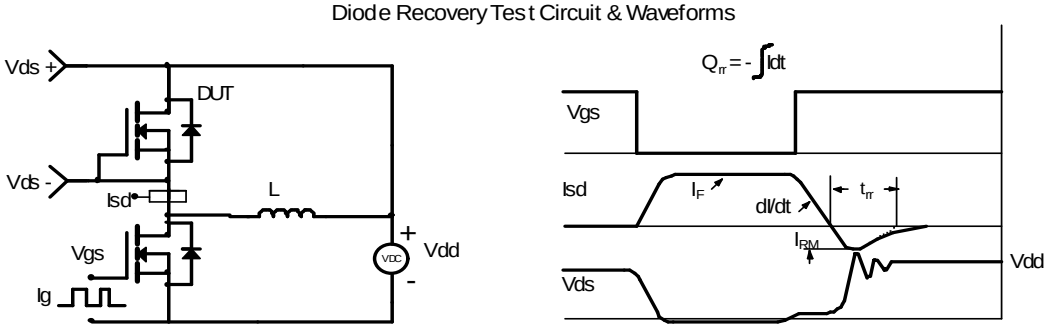
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



ALPHA & OMEGA SEMICONDUCTOR

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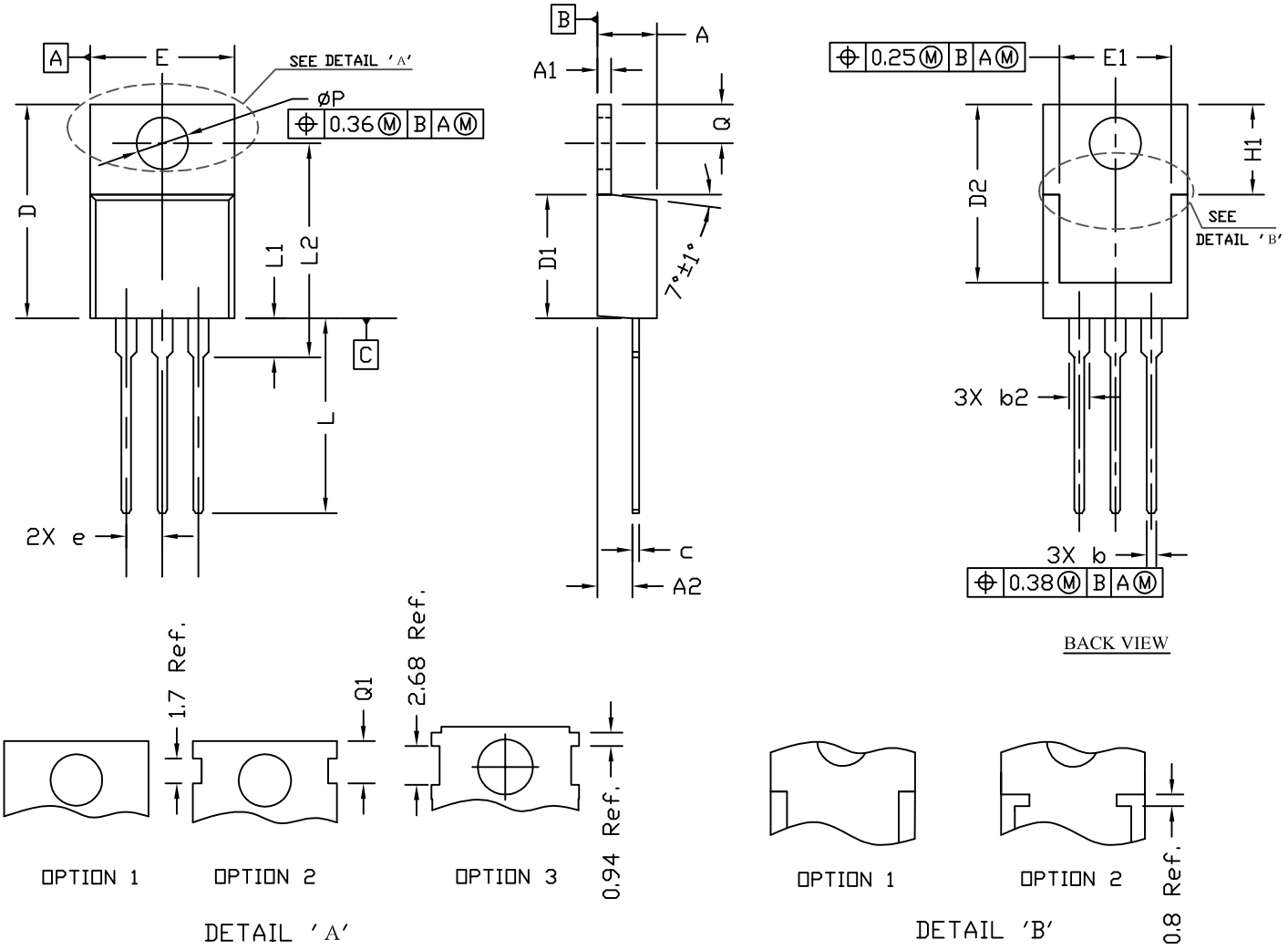
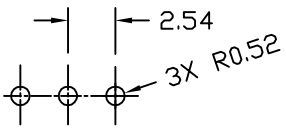
TO220 PACKAGE OUTLINE



RECOMMENDATION OF HOLE PATTERN



UNIT: mm

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.30	4.45	4.72	0.169	0.175	0.186
A1	1.15	1.27	1.40	0.045	0.050	0.055
A2	2.20	2.67	2.90	0.087	0.105	0.114
b	0.69	0.81	0.95	0.027	0.032	0.037
b2	1.17	1.37	1.45	0.046	0.050	0.068
c	0.36	0.38	0.60	0.014	0.015	0.024
D	14.50	15.44	15.80	0.571	0.608	0.622
D1	8.59	9.14	9.65	0.338	0.360	0.380
D2	11.43	11.73	12.48	0.450	0.462	0.491
e	2.54 BSC			0.100 BSC.		
E	9.66	10.03	10.54	0.380	0.395	0.415
E1	6.22	---	---	0.245	---	---
H1	6.10	6.30	6.50	0.240	0.248	0.256
L	12.27	12.82	14.27	0.483	0.505	0.562
L1	2.47	---	3.90	0.097	---	0.154
L2	---	---	16.70	---	---	0.657
Q	2.59	2.74	2.89	0.102	0.108	0.114
øP	3.50	3.84	3.89	0.138	0.151	0.153
Q1	2.70	---	2.90	0.106	---	0.114

NOTE
1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH SHOULD BE LESS THAN 6 MIL.
2. TOLERANCE 0.100 MILLIMETERS UNLESS OTHERWISE SPECIFIED.
3. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.